**Product data sheet** 

## 1. General description

PNP low  $V_{CEsat}$  transistor in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

#### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- Higher efficiency leading to less heat generation
- Reduced printed-circuit board requirements.
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- Power management
  - DC/DC converters
  - · Supply line switching
  - Battery charger
  - · LCD backlighting.
- Peripheral drivers
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - · Inductive load driver (e.g. relays, buzzers and motors).

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-30	V
I <sub>C</sub>	collector current		[1]	-	-	-3	Α
I <sub>CM</sub>	peak collector current	limited by T <sub>j(max)</sub>		-	-	-5	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C		-	80	107	mΩ

[1] Device mounted on a ceramic printed-circuit board 7 cm<sup>2</sup>, single-sided copper, tin-plated.



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		, , , , , , , , , , , , , , , , , , ,
3	В	base	3 2 1	B—[
			SOT89	sym132

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PBSS5330X-Q	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBSS5330X-Q	%1S

[1] % = placeholder for manufacturing site code

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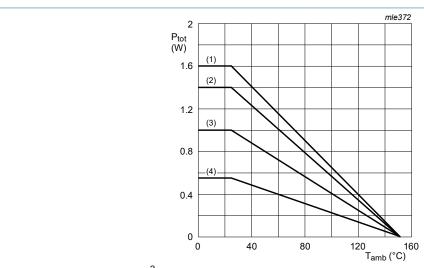
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-30	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current		[1]	-	-3	Α
I <sub>CM</sub>	peak collector current	limited by T <sub>j(max)</sub>		-	-5	Α
l <sub>B</sub>	base current			-	-0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	550	mW
			[3]	-	1	W
			[4]	-	1.4	W
			[1]	-	1.6	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on a ceramic printed-circuit board 7 cm<sup>2</sup>, single-sided copper, tin-plated.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup> [3]
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



- (1) Ceramic PCB; 7 cm<sup>2</sup> mounting pad for collector (2) FR4 PCB; 6 cm<sup>2</sup> copper mounting pad for collector (3) FR4 PCB; 1 cm<sup>2</sup> copper mounting pad for collector
- (4) Standard footprint

**Power derating curves** Fig. 1.

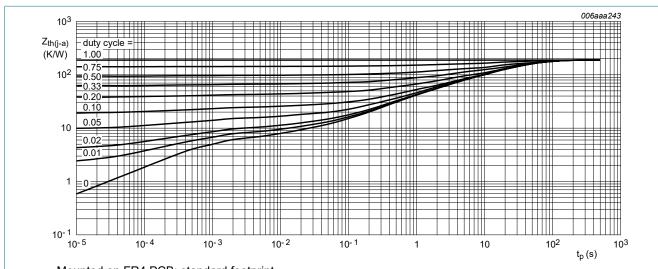
30 V, 3 A PNP low VCEsat transistor

#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

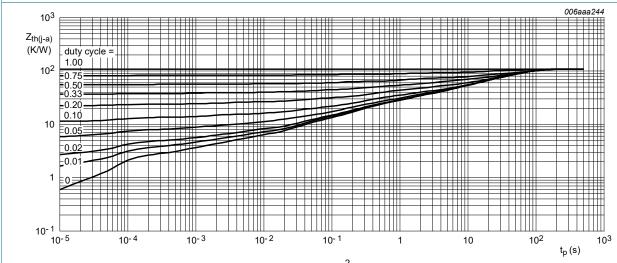
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from		[1]	-	-	225	K/W
	junction to ambient		[2]	-	-	125	K/W
			[3]	-	-	90	K/W
		[4	[4]	-	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. Device mounted on a ceramic printed-circuit board 7 cm<sup>2</sup>, single-sided copper, tin-plated. [3]
- [4]



Mounted on FR4 PCB; standard footprint.

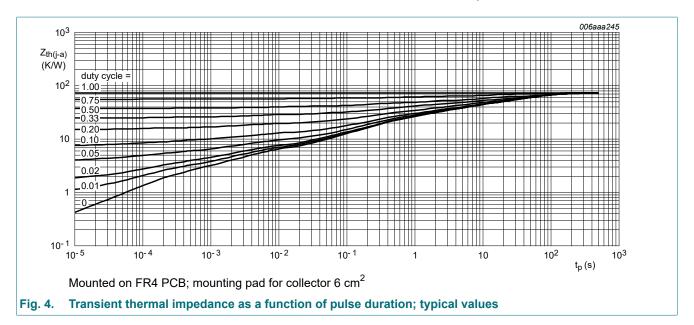
Transient thermal impedance as a function of pulse duration; typical values Fig. 2.



Mounted on FR4 PCB; mounting pad for collector 1 cm<sup>2</sup>

Transient thermal impedance as a function of pulse duration; typical values

#### 30 V, 3 A PNP low VCEsat transistor



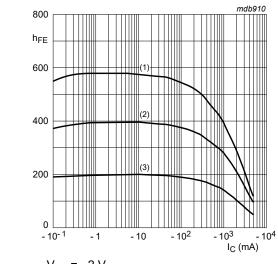
30 V, 3 A PNP low VCEsat transistor

## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
curren	current	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	200	-	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -0.5 A; T <sub>amb</sub> = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	175	-	450	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	140	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -3 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	-	-	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = -0.5 A; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-	-70	mV
	saturation voltage	I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-	-130	mV
		$I_C = -2 \text{ A}; I_B = -100 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-240	mV
		$I_C = -3 \text{ A}$ ; $I_B = -300 \text{ mA}$ ; pulsed; $t_p \le$	-	-	-320	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	80	107	mΩ
V <sub>BEsat</sub>	base-emitter saturation	I <sub>C</sub> = -2 A; I <sub>B</sub> = -100 mA; T <sub>amb</sub> = 25 °C	-	-	-1.1	V
	voltage	$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -1 A; T <sub>amb</sub> = 25 °C	-1	-	-	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	45	pF

#### 30 V, 3 A PNP low VCEsat transistor

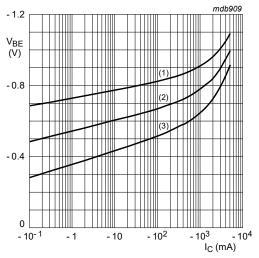


$$V_{CE} = -2 V$$
  
(1)  $T_{amb} = 100 \, ^{\circ}C$ 

$$(1) I_{amb} = 100 °C$$

(1) 
$$T_{amb} = 760^{\circ} \text{C}$$
  
(2)  $T_{amb} = 25^{\circ} \text{C}$   
(3)  $T_{amb} = -55^{\circ} \text{C}$ 

Fig. 5. DC current gain as a function of collector current; typical values

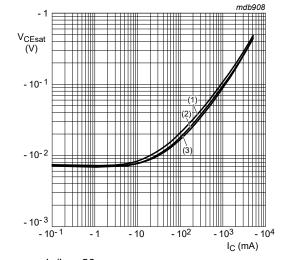


$$V_{CF} = -2 V$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Base-emitter voltage as a function of collector Fig. 6. current; typical values



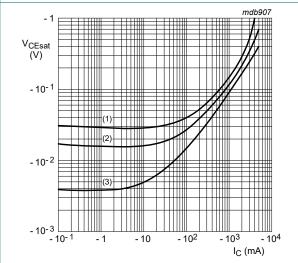
$$I_C/I_B = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



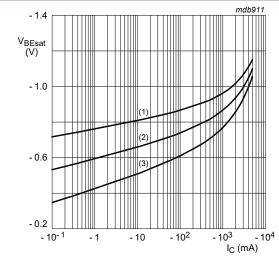
$$(1) I_{\rm C}/I_{\rm B} = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

#### 30 V, 3 A PNP low VCEsat transistor



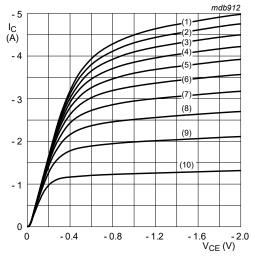
 $I_{\rm C}/I_{\rm B} = 20$ 

(1)  $T_{amb} = -55$  °C

(2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values



 $T_{amb}$  = 25 °C

(1)  $I_B = 53.0 \text{ mA}$ 

 $(2) I_B = 47.7 \text{ mA}$ 

 $(3) I_B = 42.4 \text{ mA}$ 

 $(4) I_B = 37.1 \text{ mA}$ 

 $(5) I_B = 31.8 \text{ mA}$ (6)  $I_B = 26.5 \text{ mA}$ 

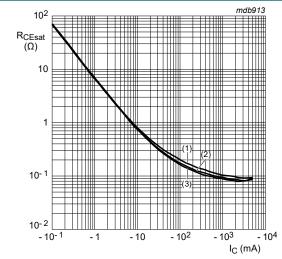
 $(7) I_B = 21.2 \text{ mA}$ 

(8)  $I_B = 15.9 \text{ mA}$ 

 $(9) I_B = 10.6 \text{ mA}$ 

 $(10) I_B = 5.3 \text{ mA}$ 

Fig. 10. Collector current as a function of collectoremitter voltage; typical values

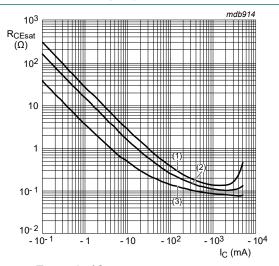


 $I_C/I_B = 20$ 

 $(1) T_{amb} = 100 °C$ 

(2)  $T_{amb} = 25 \,^{\circ}C$ (3)  $T_{amb} = -55 \,^{\circ}C$ 

Fig. 11. Equivalent on-resistance as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C.$  (1)  $I_{C}/I_{B} = 10$ 

(2)  $I_C/I_B = 5$ 

(3)  $I_C/I_B = 1$ 

Fig. 12. Equivalent on-resistance as a function of collector current; typical values

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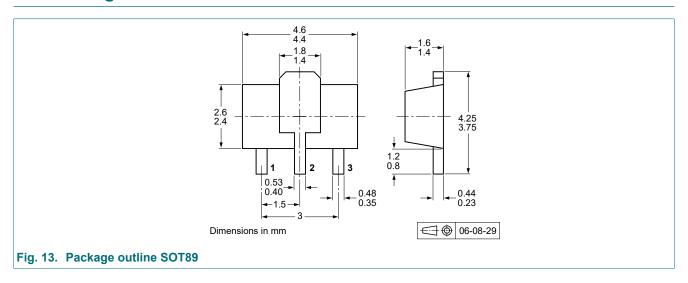
30 V, 3 A PNP low VCEsat transistor

### 11. Test information

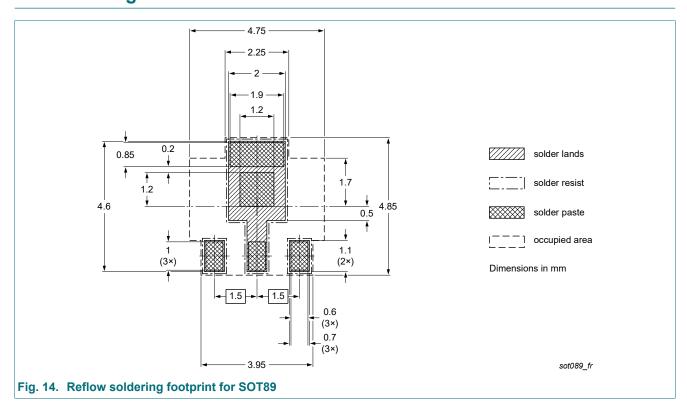
#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 -Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

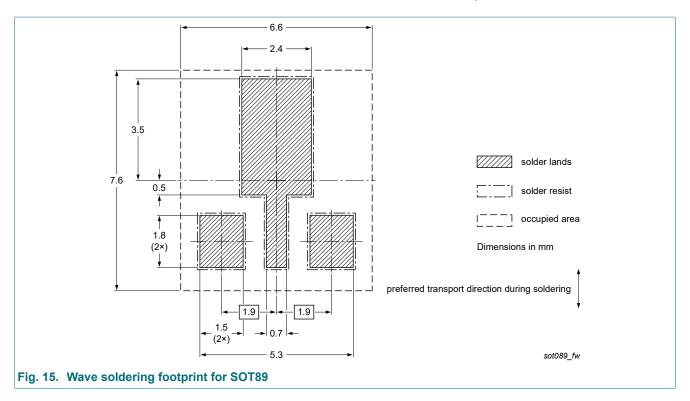
## 12. Package outline



## 13. Soldering



### 30 V, 3 A PNP low VCEsat transistor



30 V, 3 A PNP low VCEsat transistor

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5330X-Q v.1	20250813	Product data sheet	-	-

#### 30 V, 3 A PNP low VCEsat transistor

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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# PBSS5330X-Q

30 V, 3 A PNP low VCEsat transistor

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 13 August 2025

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